

QSI LASER DIODE SPECIFICATIONS FOR APPROVAL

Customer :

Model : QL65E7SB

Signature of Approval

Approvaed by _____

Checked by _____

Issued by _____

Approval by Customer



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QL65E7SB

InGaAIP Laser Diode

Quantum Semiconductor International Co., Ltd.

2003.Rev 0

◆ OVERVIEW

QL65E7SB is a MOCVD grown 650nm band *InGaAIP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 7mW and low operating current for optoelectronic devices such as Pick-up & Bar Code Reader.

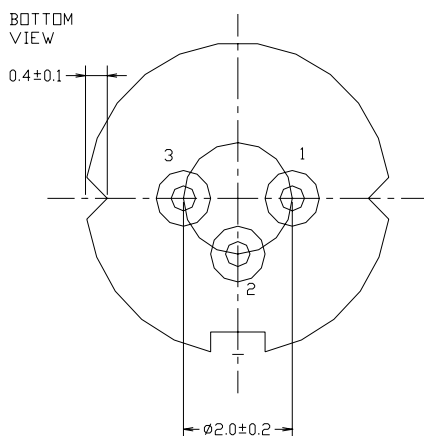
◆ APPLICATION

- Optical Pick-up (Combo type : DVD+CDRW)
- Bar Code Reader
- Laser Module

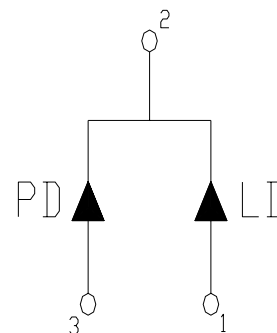
◆ FEATURES

- Visible Light Output : $\lambda_p = 650 \text{ nm}$
- Optical Power Output : 7mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION



Bottom View



Pin Configuration

◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	P	7	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +70	°C
Storage Temperature	Tstg	-40 ~ +85	°C

◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	7	-	mW	-
Threshold Current	Ith	-	30	45	mA	-
Operating Current	Iop	-	45	55	mA	Po=7mW
Operating Voltage	Vop	-	2.2	2.6	V	Po=7mW
Lasing Wavelength	λ_p	645	655	660	nm	Po=7mW
Beam Divergence	$\theta_{ }$	7	8	10	deg	Po=7mW
	θ_{\perp}	25	29	32	deg	Po=7mW
Beam Angle	$\Delta\theta_{ }$	-	-	±1.5	deg	Po=7mW
	$\Delta\theta_{\perp}$	-	-	±2.5	deg	Po=7mW
Monitor Current	Im	0.1	0.2	0.5	mA	Po=7mW
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	±60	μm	
Astigmatism	As			10	μm	

NOTICE : QL65D6SA to be operated on APC circuit.

The above product specifications are subject to change without notice.

◆PACKING

